

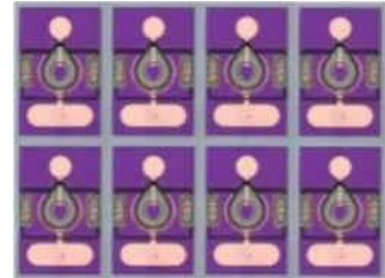


10Gbps 1260-1620nm InGaAs PIN Photodiode Chip

Part No. PDC-13A10G

Features

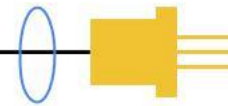
- 1310nm/1550nm InGaAs PIN photodiode chip
- Data rate up to 10Gbps
- High responsivity at 1310nm/1550nm
- Optimized for fiber optic application
- Low dark current and low capacitance



Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage temperature	-40	100	°C	
Operating temperature	-40	85	°C	
Forward current		10	mA	
Reverse current		2	mA	
Reverse voltage		20	V	
Optical power		2	mW	

Electro-Optical Characteristics (T = 25°C)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Active diameter	Φ		50		μm	
Responsivity	R	0.9	1.1		A/W	$V_R=1.5V, \lambda=1550\text{nm}@25^\circ\text{C}$
		0.8	0.9			$V_R=1.5V, \lambda=1310\text{nm}@25^\circ\text{C}$
Dark current	I_D		0.2	1	nA	$V_R=5V$
Breakdown voltage	V_{BD}	25	40		V	$I_R=10\mu\text{A}$
Capacitance	C		0.25	0.27	pF	$V_R=1.5V, f=1\text{MHz}$
			0.20			$V_R=5V, f=1\text{MHz}$
bandwidth	BW		9		GHz	$V_R=5V$



Typical Characteristics

Fig. 1 Typical Dark Current vs. Forward Current

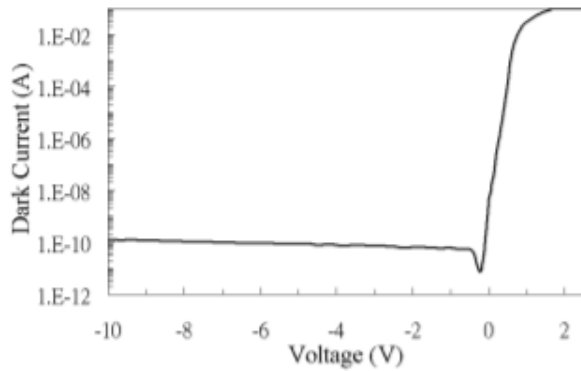


Fig. 2 Typical Photo-Current

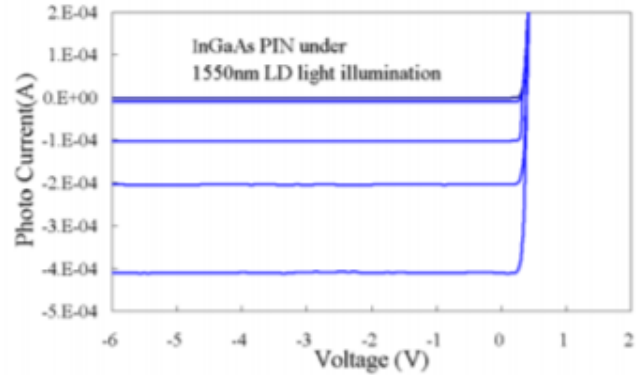


Fig. 3 Typical Breakdown Curve

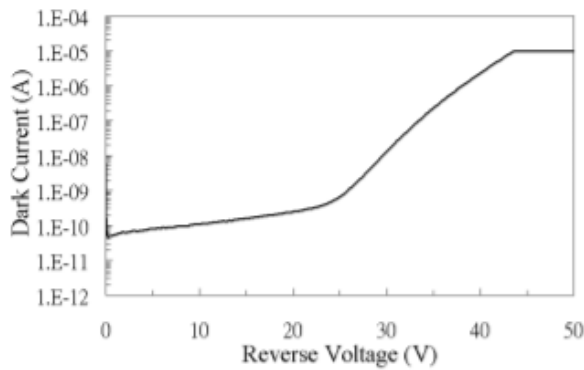
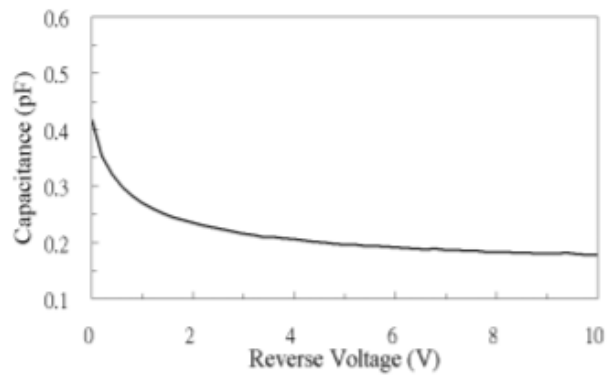
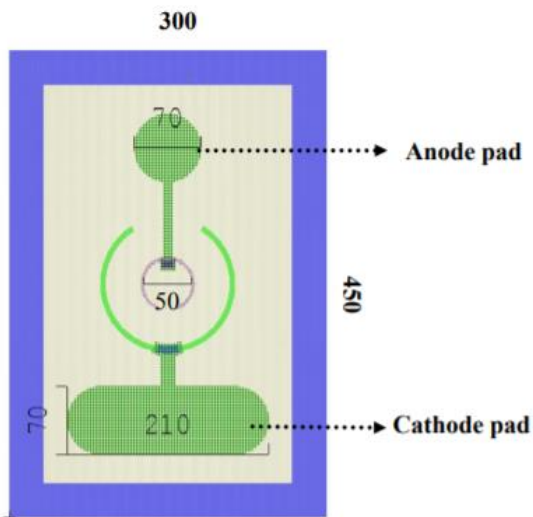


Fig. 4 Typical C-V Curve



Outline Diagram



- Chip size: 450 μ m x 300 μ m typical
- Chip thickness: 200 μ m \pm 12.5 μ m
- Sensitive area: Typical 50 μ m in diameter

Note: Specifications are subject to change without notice.